WHAT IS CLAIMED IS:

1. An ablation method of applying a laser beam to a die attach film to perform ablation, said ablation method comprising:

a protective film forming step of applying a liquid resin containing a fine powder of oxide having absorptivity to the wavelength of said laser beam to at least a subject area of said die attach film to be ablated, thereby forming a protective film containing said fine powder on at least said subject area of said die attach film; and

a laser processing step of applying said laser beam to said subject area coated with said protective film, thereby performing ablation through said protective film to said subject area of said die attach film after performing said protective film forming step.

2. The ablation method according to claim 1, wherein said fine powder of said oxide has an average particle size smaller than a spot diameter of said laser beam.

3. The ablation method according to claim 1, wherein

the wavelength of said laser beam is 355 nm or less;

said fine powder of said oxide includes a metal oxide selected from the group consisting of Fe_2O_3, ZnO, TiO_2, CeO_2, CuO, Cu_2O, and MgO; and

said liquid resin includes polyvinyl alcohol.

WHAT IS CLAIMED IS:

1. An ablation method for a die attach film of applying a laser beam to the die attach film attached to a back side of a wafer divided into individual devices, thereby performing ablation, the ablation method comprising:

a protective film forming step of applying a liquid resin to at least a subject area of the die attach film to be ablated, the liquid resin containing a fine powder of oxide having absorptivity to a wavelength of the laser beam, thereby forming a protective film containing the fine powder; and

a laser processing step of applying the laser beam to the subject area of the die attach film coated with the protective film, along a division groove dividing the wafer into the individual devices, after performing the protective film forming step, thereby performing ablation to the die attach film, thereby dividing the die attach film by corresponding to the individual devices;

the fine powder of the oxide having an average

particle size smaller than a spot diameter of the laser beam, and the spot diameter of the laser beam being set to 10 μm or less;

the wavelength of the laser beam being set to 355 nm or less, and the fine powder of the oxide including metal oxide selected from the group consisting of Fe_2O3, ZnO, TiO_2, CeO_2, CuO, Cu_2O, and MgO.

2. The ablation method for a die attach film according to claim 1, further comprising:

a supporting step of attaching the die attach film to the back side of the wafer which is divided into the individual devices by a dicing before grinding process, and attaching the die attach film to an adhesive tape whose peripheral portion is supported to an annular frame, thereby supporting the wafer and the die attach film to the annular frame.